

MMST5551

NPN Small Signal Surface Mount Transistor



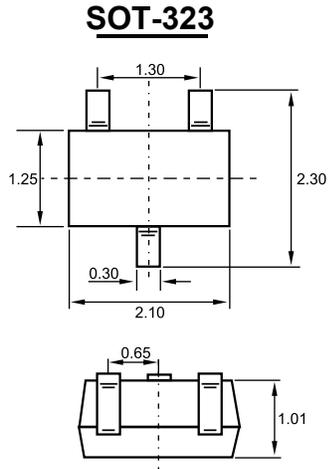
1. BASE
2. EMITTER
3. COLLECTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMST5401)
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package

Mechanical Data

- Case: SOT-323, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: K4N
- Weight: 0.006 grams (approx.)



Dimensions in inches and (millimeters)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MMST5551	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I_C	200	mA
Power Dissipation (Note 1)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	K/W
Operating and Storage and Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. Valid provided that terminals are kept at ambient temperature.
 2. Pulse test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	180	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	160	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CBO}	—	50	nA μA	$V_{CB} = 120\text{V}, I_E = 0$ $V_{CB} = 120\text{V}, I_E = 0, T_A = 100^\circ\text{C}$
Emitter Cutoff Current	I_{EBO}	—	50	nA	$V_{EB} = 4.0\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	80 80 30	— 250 —	—	$I_C = 1.0\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 5.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.15 0.20	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base- Emitter Saturation Voltage	$V_{BE(SAT)}$	—	1.0	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	6.0	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Small Signal Current Gain	h_{fe}	50	250	—	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA},$ $f = 1.0\text{kHz}$
Current Gain-Bandwidth Product	f_T	100	300	MHz	$V_{CE} = 10\text{V}, I_C = 10\text{mA},$ $f = 100\text{MHz}$
Noise Figure	NF	—	8.0	dB	$V_{CE} = 5.0\text{V}, I_C = 200\mu\text{A},$ $R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$

- Notes: 1. Valid provided that terminals are kept at ambient temperature.
2. Pulse test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.